

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07504 D T-33-15

SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC2204

2SC2220

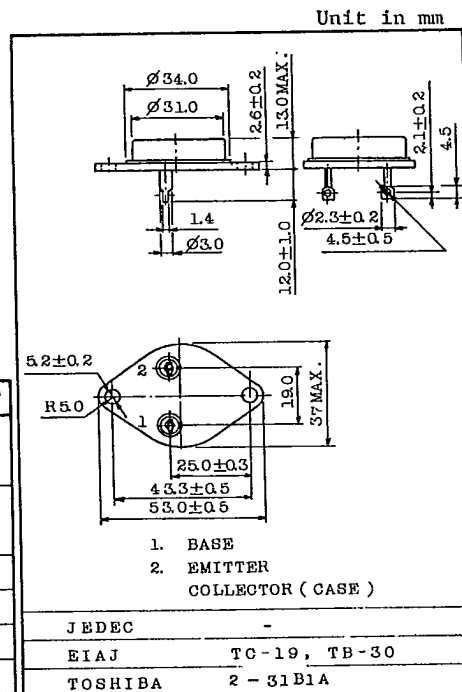
HIGH POWER SWITCHING APPLICATIONS.
HIGH FREQUENCY INVERTOR APPLICATIONS.

FEATURES :

- High Voltage : $V_{CEO}=400V(\text{Min.})$ (2SC2204)
 $V_{CEO}=300V(\text{Min.})$ (2SC2220)
 $V_{CBO}=800V(\text{Min.})$ (2SC2204)
 $V_{CBO}=500V(\text{Min.})$ (2SC2220)
- High Speed Switching : $t_f=0.7\mu s(\text{Typ.})$

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	800	V
		500	
Collector-Emitter Voltage	V_{CEO}	400	V
		300	
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	30	A
Emitter Current	I_E	-30	A
Base Current	I_B	15	A
Collector Power Dissipation	P_C	250	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65~150	$^\circ\text{C}$



Mounting kit No.AC63
Weight : 46g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=800V, I_E=0$	-	-	1.0	mA
		$V_{CB}=500V, I_E=0$	-	-	5	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	5	mA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=20mA, I_B=0$	400	-	-	V
			300	-	-	V
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=30A$	10	-	-	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}, I_C=30A, I_B=6A$	-	-	1.5	V
	Base-Emitter	$V_{BE(sat)}, I_C=30A, I_B=6A$	-	-	2.0	V
Collector Output Capacitance	C_{ob}	$V_{CB}=50V, I_E=0, f=1MHz$	-	400	-	pF
Switching Time	Turn-on Time	t_{on}	-	1.2	1.5	μs
	Storage Time	t_{stg}	-	3.0	4.0	μs
	Fall Time	t_f	-	0.7	1.0	μs